

EL46567 6034

Sheet 1 of 2

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET M112-1421		SERIAL NO. Filed Herewith	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Micron Technology, Inc.		FILING DATE Filed Herewith	
				GROUP			
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
JK	AA 4,954,867	09/04/90	Hosaka	257	639		
JK	AB 5,441,797	08/15/95	Hogan et al.	428	209		
JK	AC 5,472,827	12/05/95	Ogawa et al.	430	315		
JK	AD 5,674,356	10/07/97	Nagayama	438	694		
JK	AE 5,710,067	01/20/98	Foot et al.	438	636		
JK	AF 5,731,242	03/24/98	Parai et al.	438	546		
JK	AG 5,741,721	04/21/98	Stevens	438	396		
JK	AH 5,759,755	06/02/98	Park et al.	430	512		
JK	AI 5,818,052	11/17/98	McTeer	257	437		
	AJ						
	AK						
FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
JK	AL JP06067019A	1/92	Japan (Abstract)				
JK	AM 0 471 185 A2	2/92	EPO				
JK	AN 0 588 087 A2	3/92	EPO				
JK	AO 0 588 087 A3	3/92	EPO				
	AP						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)							
JK	AR	ARTICLE: Beacher, C. et al., "Dielectric antireflective coatings for DUV lithography", Solid State Technology (March 1997), pp. 109-114.					
JK	AS	ARTICLE: Dammel, R. R. et al., "Dependence of Optical Constants of AZ® BARLI™ Bottom Coating on Back Conditions", SPIE Vol. 3049 (1997), pp. 963-973.					
JK	AT	TEXT: Heavens, O. S., "Optical Properties of Thin Solid Films", pp. 48-49. Dover Publications 1991					
EXAMINER		JSC Eshet		DATE CONSIDERED		2/28/01	
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 600; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

EL46567 6034

Sheet 2 of 2

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
M122-1427SERIAL NO.  
Filed-Appl. No.LIST OF ART CITED BY APPLICANT  
(Use several sheets if necessary)APPLICANT  
Micron Technology, Inc.

09/559903

FILING DATE  
Filed Herewith

GROUP

## U.S. PATENT DOCUMENTS

*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA					
	AB					
	AC					
	AD					
	AE					
	AF					
	AG					
	AH					
	AI					
	AJ					
	AK					

## FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
	AL						
	AM						
	AN						
	AO						
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## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

932	AR	TEXT: Jenkins, F. et al., "Fundamentals of Optics", Properties of Light, pp. 9-10.
		McGraw Hill 1976
932	AS	TEXT: Wolf, S. et al., "Silicon Processing for the VLSI Era", Vol. 1, pp. 437-441.
		Lattice Press 1986
	AT	

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DATE CONSIDERED

9/28/01

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1427		SERIAL NO. 09/559,903	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Zhiping Yin et al.		FILING DATE April 26, 2000	
				GROUP 2815			
FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
92	AA	0 942 330 A1	9/99	EPO			
91	AB	00-050993/JP9750993	2/97	Japan			
91	AC	4062441/726-244172	9/94	Japan			
91	AD	593,737	10/47	GB			
91	AE	5-263255/JP9263255	10/93	Japan			
91	AF	0 464 515 A3	1/92	EPO			
91	AG	0 771 886 A1	5/97	EPO			
91	AH	63-157443/JP63157443 A	6/88	JP			
OTHER REFERENCES (including Author, Title, Date, Foreign Pat. No., etc.)							
91	AI	Robert Withall et al., "Matrix Reactions of Methylsilanes and Oxygen Atoms", 1988 American Chemical Society, pp 594-607					
91	AJ	Weidman, T. et al., "New Photodefinable Glass Etch Masks for Entirely Dry Photolithography: Plasma Deposited Organosilicon Hydride Polymers", Appl. Phys. Lett., Vol. 62, No. 4, Jan. 25, 1993, pp. 372-374.					
91	AK	Weidman, T. et al., "All Dry Lithography: Applications of Plasma Polymerized Methylsilane as a Single Layer Resist and Silicon Dioxide Precursor", J. Photopolym. Sci. Technol., Vol. 8, No. 4, 1995, pp. 679-686.					
91	AL	Joubert, O. et al., "Application of Plasma Polymerized Methylsilane in an All Dry Resist Process for 193 and 248nm Lithography", Microelectronic Engineering 30 (1996), pp. 275-278.					
91	AM	Ajay M. Joshi et al., "Plasma Deposited Organosilicon Hydride Network Polymers as Versatile Resists for Entirely Dry Mid-Deep UV Photolithography", SPIE Vol 1925/709; pp. 709-720 January 26, 1993					
91	AN	M. Matsuo et al., "A Highly Reliable Self-planarizing Low-k Intermetal Dielectric for Sub-quarter Micron Interconnects", IEEE 797 pp 31.6.1-31.6.4 July 1997					
91	AO	O. Horie et al., "Kinetics and Mechanism of the Reactions of O(P) with SiH <sub>4</sub> , CH <sub>3</sub> SiH <sub>3</sub> , (CH <sub>3</sub> ) <sub>2</sub> SiH <sub>2</sub> and (CH <sub>3</sub> ) <sub>3</sub> SiH", 1991 American Chemical Society, pp 4393-4400					
91	AP	McClatchie, S. et al., "Low Dielectric Constant Flowfill Technology for IMD Applications", Proceed. of 3d Internat. Dielectrics for ULSI Multilevel Interconnection Conf, Santa Clara, CA, Feb. 1997, pp. 34-40.					
91	AQ	Beckman, K. et al., "Sub-Micron Gap Fill and In-Situ Planarization Using Flowfill™ Technology", ULSI Conf, Portland, OR, Oct. 1995, pp. 1-7.					
91	AR	Kiermarz, A. et al., "Planarization for Sub-Micron Devices Utilizing a New Chemistry", DUMIC Conf, California, Feb. 1995, pp. 1-10.					
91	AS	IBM Technical Disclosure Bulletin "Low-Temperature Deposition of SiO <sub>2</sub> , Si3N4 or SiO <sub>2</sub> -Si3N4", Vol. 28, No. 9, p. 4170, Feb. 1986					
91	AT	TEXT: Ralla, K. et al., "Introduction to Materials Science and Engineering", 1976 John Wiley & Sons, Inc., pp. 312-313.					
91	AU	ABSTRACT: Loboda, M. et al., "Using Dimethylsilane to Improve Safety, Throughput and Versatility in PECVD Processes", Electrochemical Society Meeting Abstract No. 358, 191 <sup>st</sup> Meeting, Montreal, Quebec, Vol. MA 97-1, 1997, page 454.					
91	AV	Laxman, R. et al., "Synthesizing Low-K CVD Materials for Fab Use", Semiconductor Internat., Nov. 2000, pp. 95-102 (printed from www.semiconductor-intel.com).					
91	A	Anonymous, "New Gas Helps Make Faster ICs", Machine Design, Vol. 71, Iss. 21, Nov. 4, 1999, p. 118.					
91	AX	Julius Grant, "Hack's Chemical Dictionary", McGraw-Hill Book Company 1969, Fourth Edition, page 27.					
EXAMINER 91SCB/A				DATE CONSIDERED 5/20/02			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Form PTO-1219		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M21-1427		SERIAL NO. 09-527,703	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Zhang Yie et al.		GROUP 2815	
				FILING DATE April 28, 2000			
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
YCE	AA	6,113,618	10-2000	Sulzer			
	AB	5,094,217	11-1999	Ng			
	AC	5,983,319	11-1999	Kakamu et al.			
	AD	5,147,388	05-1998	Kraters et al.			
	AE	5,630,887	06-1997	Roman et al.			
	AF	5,128,335	03-1996	Lin			
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	AL						
FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
	AM					Yes	No
	AN						
	AO						
	AP						
	AO						
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
YCE	AR	Wolf, S. "Silicon Processing for the VLSI Era," Vol. 1, pp. 677-713.		Lattice Press 1986			
	AS	Wolf, S. "Silicon Processing for the VLSI Era," Vol. 2, pp. 48-49 and 135.		Lattice Press 1986			
EXAMINER YCE/mo				DATE CONSIDERED 2/16/04			
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